

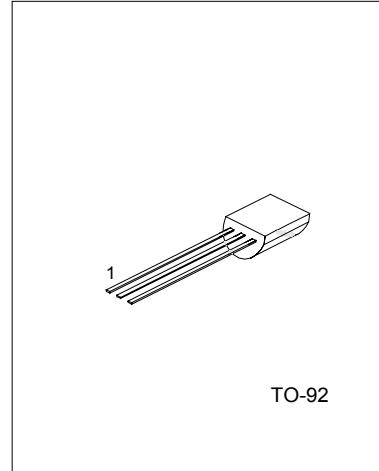
UTC BC337/338 NPN EPITAXIAL SILICON TRANSISTOR

SWITCHING AND AMPLIFIER APPLICATIONS

FEATURES

*Suitable for AF-Driver stages and low power output stages

*Complement to BC327/328



1: COLLECTOR 2: BASE 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-emitter voltage : BC337 : BC338	V _{CES}	50 30	V V
Collector-emitter voltage : BC337 : BC338	V _{CEO}	45 25	V V
Emitter-base voltage	V _{EBO}	5	V
Collector current (DC)	I _c	800	mA
Collector dissipation	P _c	625	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage : BC337 : BC338	BV _{CEO}	I _c =10mA, I _B =0	45 25			V V
Collector-emitter breakdown voltage : BC337 : BC338	BV _{CES}	I _c =0.1mA, V _{BE} =0	50 30			V V
Emitter-base breakdown voltage	BV _{EBO}	I _E =0.1mA, I _c =0	5			V
Collector Cut-off Current : BC337 : BC338	I _{CEs}	V _{CE} =45V, I _B =0 V _{CE} =25V, I _B =0		2 2	100 100	nA nA
DC current gain	h _{FE1} h _{FE2}	V _{CE} =1V, I _c =100mA V _{CE} =1V, I _c =300mA	100 60		630	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _B =50mA			0.7	V

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Base-emitter on voltage	V _{BE(on)}	V _{CE} =1V, I _c =300mA			1.2	V
Current gain bandwidth product	f _T	V _{CE} =5V, I _c =10mA, f=50MHz		100		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		12		pF

CLASSIFICATION OF h_{FE1}

RANK	16	25	40
h _{FE1}	100-250	160-400	250-630